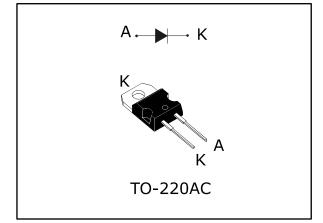


STPSC8065

650 V power Schottky silicon carbide diode

Datasheet - production data



Features

- No or negligible reverse recovery
- Switching behavior independent of temperature
- Dedicated to PFC applications
- High forward surge capability
- Operating T_j from -40 °C to 175 °C
- ECOPACK®2 compliant component

This is information on a product in full production.

Description

The SiC diode is an ultra high performance power Schottky diode. It is manufactured using a silicon carbide substrate. The wide band gap material allows the design of a Schottky diode structure with a 650 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

Especially suited for use in PFC applications, this ST SiC diode will boost performance in hard switching conditions. Its high forward surge capability ensures good robustness during transient phases.

Symbol	Value			
IF(AV)	8 A			
V _{RRM}	650 V			
T _j (max.)	175 °C			
V _F (typ.)	1.30 V			

Table 1: Device summary

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1 Characteristics

Table 2: Absolute ratings (limiting values at 25 °C, unless otherwise specified)

Symbol	Pa	Value	Unit	
Vrrm	Repetitive peak reverse voltage	9	650	V
I _{F(RMS)}	Forward rms current		22	Α
I _{F(AV)}	Average forward current $T_{\rm C} = 150 ^{\circ}{\rm C}^{(1)}$, DC current		8	А
IFRM	Repetitive peak forward current $T_c = 150 \ ^{\circ}C, T_j = 175 \ ^{\circ}C, \delta = 0.1$		36	А
		t_p = 10 ms sinusoidal, T_c = 25 $^{\circ}\text{C}$	46	
IFSM	I _{FSM} Surge non repetitive forward current	t_p = 10 ms sinusoidal, T_c = 125 °C	38	А
	$t_p = 10 \ \mu s \ square, \ T_c = 25 \ ^\circ C$	200		
T _{stg}	Storage temperature range		-65 to +175	°C
Tj	Operating junction temperature ⁽²⁾		-40 to +175	°C

Notes:

 $^{(1)}\mbox{Value}$ based on $R_{th(j\text{-}c)}$ max.

 $^{(2)}(dP_{tot}/dT_j) < (1/R_{th(j-a)})$ condition to avoid thermal runaway for a diode on its own heatsink.

Table 3: Thermal parameters

Symbol Parameter	Parameter	Value		Unit
	Farameter		Max.	Unit
R _{th(j-c)}	Junction to case	1.1	1.65	°C/W

Table 4: Static electrical characteristics

Sy	mbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
IR ⁽¹⁾	_ (1)	Deverse la chara averant	T _j = 25 °C		-	2	105	
	Reverse leakage current	T _j = 150 °C	Vr = Vrrm	-	20	750	μA	
V _F ⁽²⁾	Forward voltage drop	Tj = 25 °C	I _F = 8 A	-	1.30	1.45	V	
		T _j = 150 °C		-	1.45	1.65		
		Tj = 175 °C		-	1.50			

Notes:

 $^{(1)}$ Pulse test: tp = 5 ms, δ < 2% $^{(2)}$ Pulse test: tp = 500 µs, δ < 2%

To evaluate the conduction losses, use the following equation:

 $P = 0.95 \text{ x } I_{F(AV)} + 0.087 \text{ x } I_{F^{2}(RMS)}$





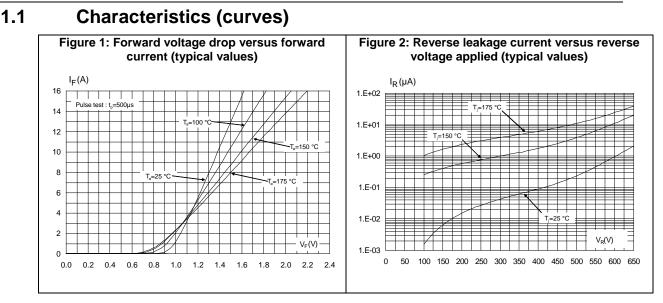
	Table 5: Dynamic electrical characteristics				
Symbol	Parameter	Test conditions	Тур.	Unit	
Q _{Cj} ⁽¹⁾	Total capacitive charge	V _R = 400 V	28	nC	
C _j Total capacitance	$V_R = 0 V$, $T_c = 25 \text{ °C}$, $F = 1 \text{ MHz}$	540	- F		
	Total capacitance	$V_R = 400 \text{ V}, \text{T}_c = 25 ^\circ \text{C}, \text{F} = 1 \text{MHz}$	45	pF	

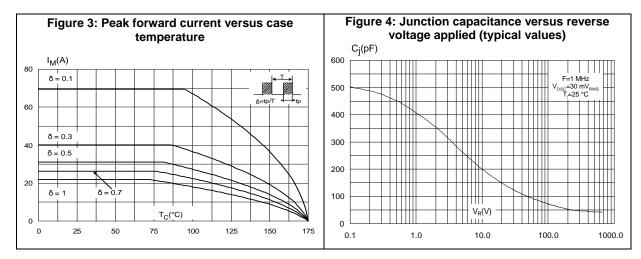
Notes:

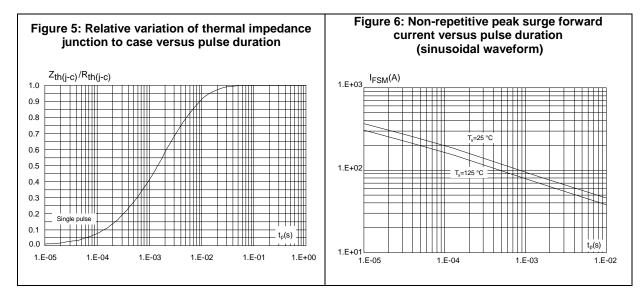
⁽¹⁾Most accurate value for the capacitive charge: $Q_{cj} = \int_0^{V_{OUT}} C_j(V_R) \bullet dV_R$



Characteristics



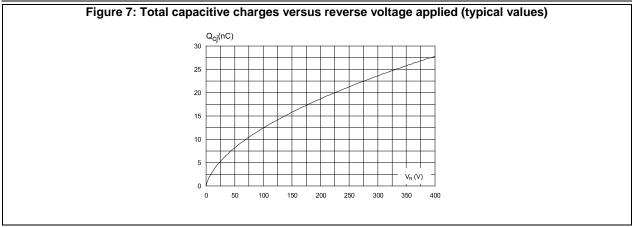




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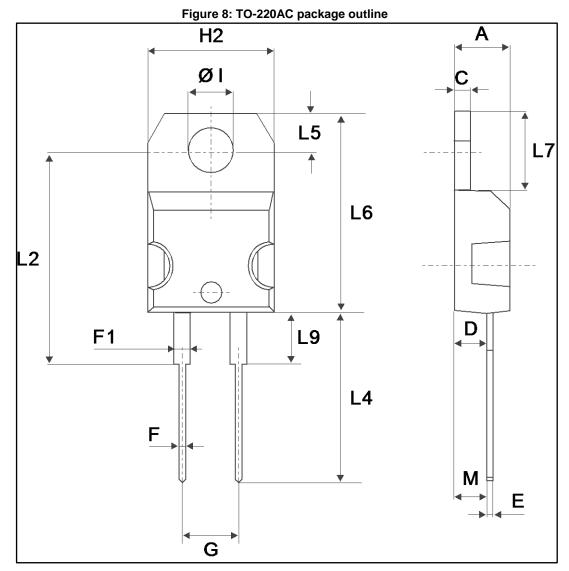


2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK[®] is an ST trademark.

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.55 N·m
- Maximum torque value: 0.7 N·m

2.1 TO-220AC package information





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Package information

	Table 6: TO-220AC package mechanical data				
Dimensions					
Ref.	Millim	Millimeters		nes	
	Min.	Max.	Min.	Max.	
А	4.40	4.60	0.173	0.181	
С	1.23	1.32	0.048	0.051	
D	2.40	2.72	0.094	0.107	
E	0.49	0.70	0.019	0.027	
F	0.61	0.88	0.024	0.034	
F1	1.14	1.70	0.044	0.066	
G	4.95	5.15	0.194	0.202	
H2	10.00	10.40	0.393	0.409	
L2	16.40) typ.	0.645 typ.		
L4	13.00	14.00	0.511	0.551	
L5	2.65	2.95	0.104	0.116	
L6	15.25	15.75	0.600	0.620	
L7	6.20	6.60	0.244	0.259	
L9	3.50	3.93	0.137	0.154	
М	2.6	typ.	0.102	typ.	
ØI	3.75	3.85	0.147	0.151	



3 Ordering information

Table 7: Ordering information					
Order code Marking Package Weight Base qty. Delivery mode					Delivery mode
STPSC8065D	PSC8065D	TO-220AC	1.86 g	50	Tube

4 Revision history

Date	Revision	Changes
13-Jun-2017	1	First issue.
18-Jul-2017	2	Updated Table 4: "Static electrical characteristics"



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